

## Features

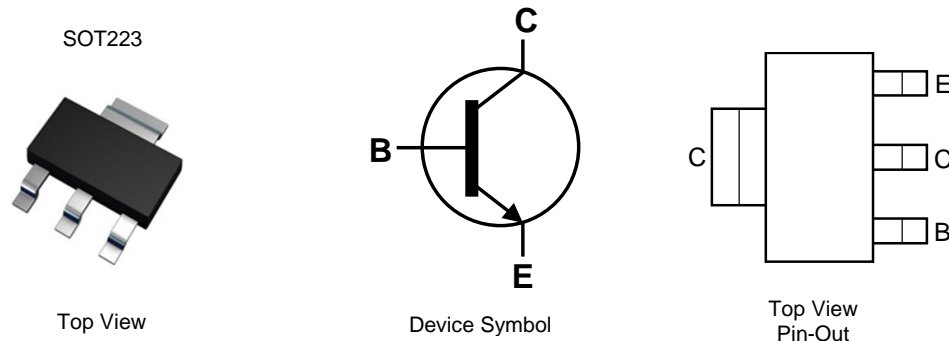
- $BV_{CEX} > 180V$
- $BV_{CEO} > 100V$
- $BV_{ECO} > 6V$
- $I_C = 3A$  High Continuous Current
- Low Saturation Voltage  $V_{CE(sat)} < 100mV @ 1A$
- $R_{CE(sat)} = 85m\Omega$
- Complementary PNP Type: ZXTP19100CG
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

## Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (Ⓢ)
- Weight: 0.112 grams (Approximate)

## Applications

- PSU Start-Up Circuit
- DC-DC Converters
- Motor Drive
- Relay, Lamp and Solenoid Drive

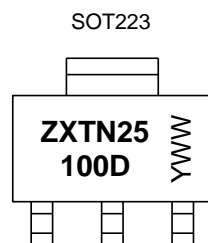


## Ordering Information (Notes 4 & 5)

| Product        | Compliance | Marking    | Reel size (inches) | Tape width (mm) | Quantity per reel |
|----------------|------------|------------|--------------------|-----------------|-------------------|
| ZXTN25100DGTA  | AEC-Q101   | ZXTN25100D | 7                  | 12              | 1,000             |
| ZXTN25100DGQTA | Automotive | ZXTN25100D | 7                  | 12              | 1,000             |

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to [http://www.diodes.com/quality/product\\_compliance\\_definitions/](http://www.diodes.com/quality/product_compliance_definitions/).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



ZXTN25100D = Product Type Marking Code  
 YWW = Date Code Marking  
 Y or  $\bar{Y}$  = Last Digit of Year (ex: 5= 2015)  
 WW or  $\bar{WW}$  = Week Code (01~53)

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                               | Symbol           | Value | Unit |
|--|------------------|-------|------|
| Collector-Base Voltage                       | V <sub>CBO</sub> | 180   | V    |
| Collector-Emitter Voltage (forward blocking) | V <sub>CEX</sub> | 180   | V    |
| Collector-Emitter Voltage                    | V <sub>CEO</sub> | 100   | V    |
| Emitter-Collector Voltage (reverse blocking) | V <sub>ECO</sub> | 6     | V    |
| Emitter-Base Voltage                         | V <sub>EBO</sub> | 7     | V    |
| Continuous Collector Current                 | I <sub>C</sub>   | 3     | A    |
| Base Current                                 | I <sub>B</sub>   | 1     | A    |
| Peak Pulse Current                           | I <sub>CM</sub>  | 3.5   | A    |

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

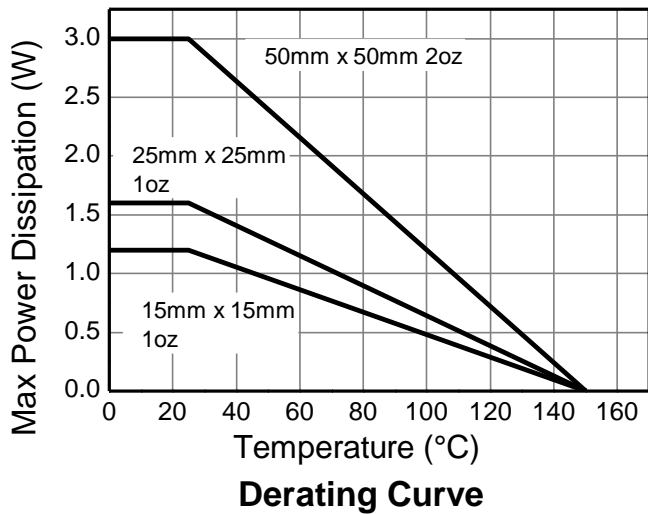
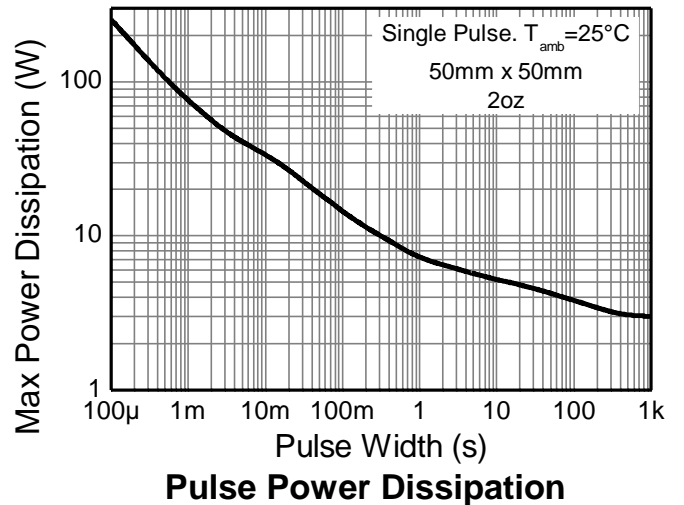
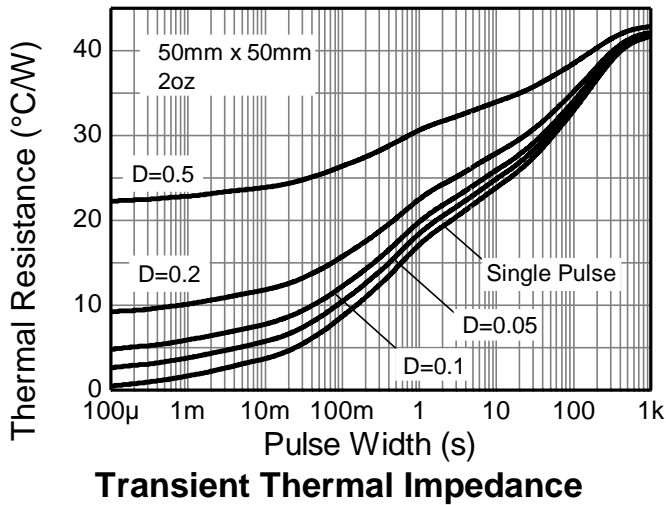
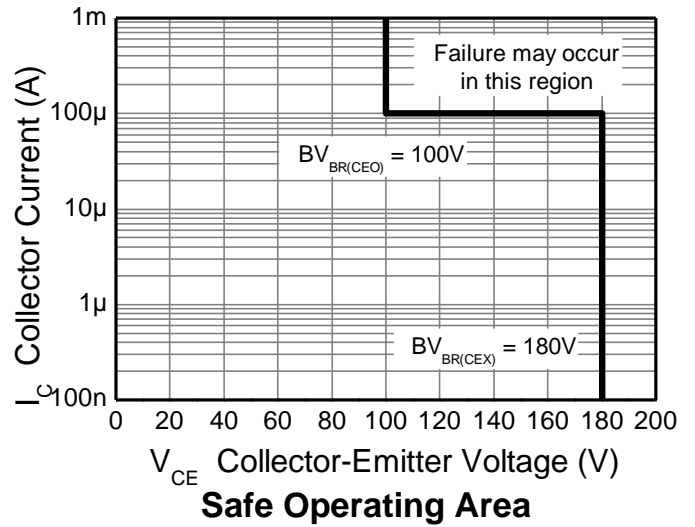
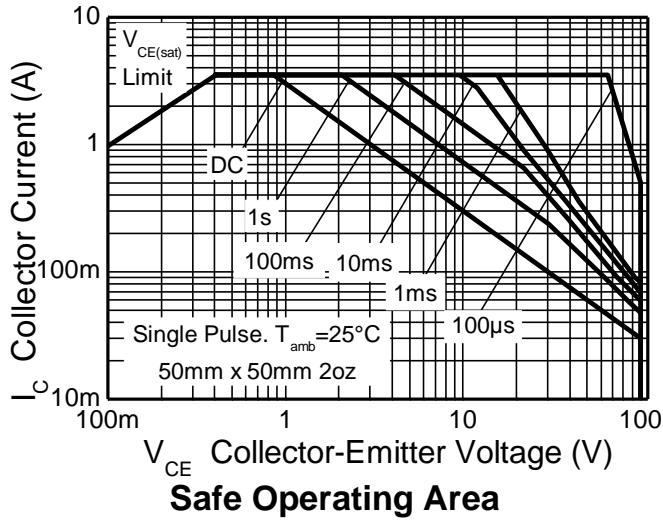
| Characteristic                               | Symbol                            | Value       | Unit       |
|--|-----------------------------------|-------------|------------|
| Power Dissipation<br>Linear Derating Factor  | P <sub>D</sub>                    | 1.2         | W<br>mW/°C |
|  |                                   | 9.6         |            |
|  |                                   | 1.6         |            |
|  |                                   | 12.8        |            |
|  |                                   | 3           |            |
| Thermal Resistance, Junction to Ambient      | R <sub>θJA</sub>                  | 24          | °C/W       |
|  |                                   | 5.3         |            |
|  |                                   | 42          |            |
|  |                                   | 104         |            |
| Thermal Resistance, Junction to Lead         | R <sub>θJL</sub>                  | 78          | °C/W       |
|  |                                   | 42          |            |
|  |                                   | 23.5        |            |
| Thermal Resistance, Junction to Solder Point | R <sub>θJS</sub>                  | 16          | °C/W       |
| Operating and Storage Temperature Range      | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C         |

**ESD Ratings** (Note 11)

| Characteristic                             | Symbol  | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | V    | 3A          |
| Electrostatic Discharge - Machine Model    | ESD MM  | 400   | V    | C           |

- Notes:
- For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
  - Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
  - Same as Note 6, except the device is mounted on 50mm x 50mm 2oz copper.
  - Same as Note 8 measured at t<5 seconds.
  - Thermal resistance from junction to solder-point (at the end of the collector lead).
  - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

**Thermal Characteristics and Derating Information** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

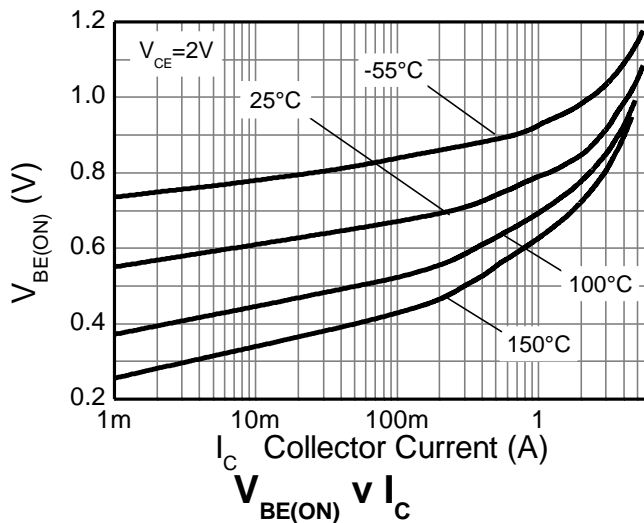
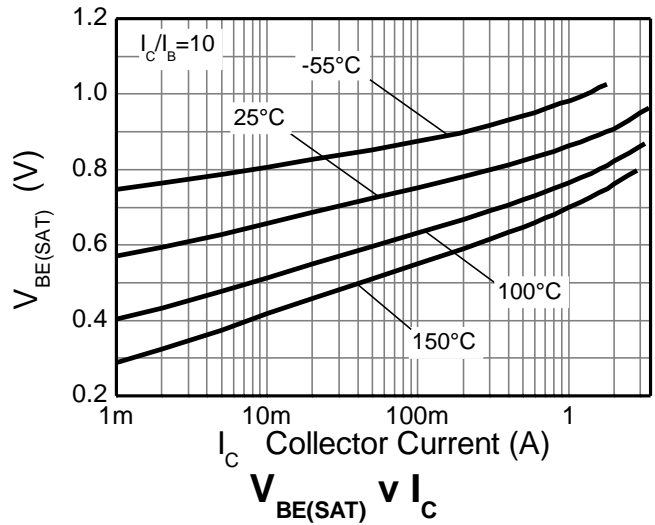
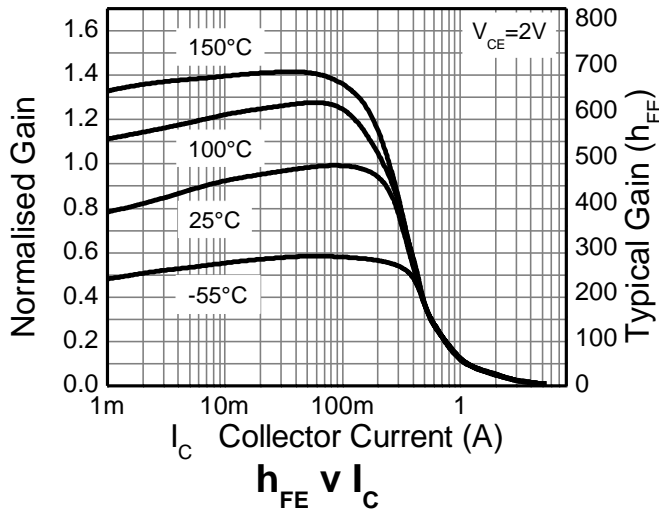
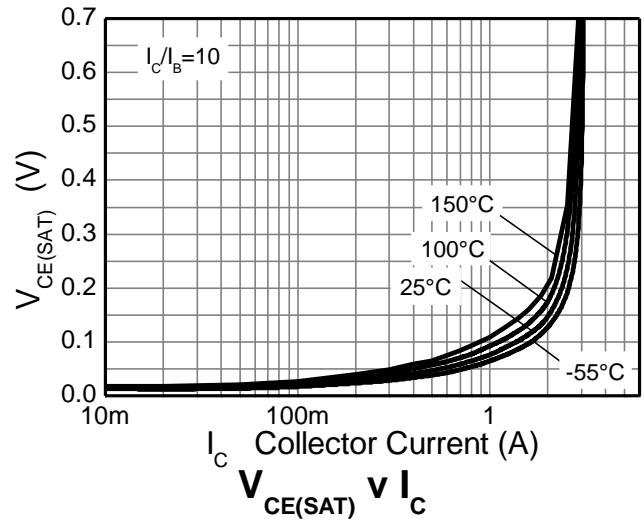
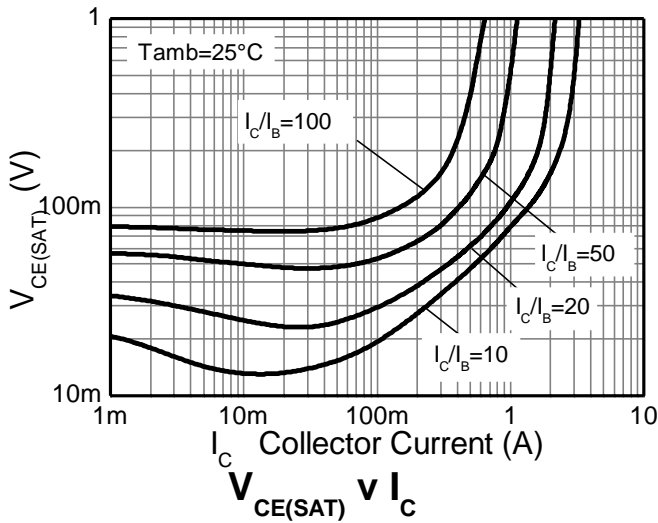


**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic   | Symbol               | Min | Typ  | Max  | Unit | Test Condition   |
|--|----------------------|-----|------|------|------|--|
| Collector-Base Breakdown Voltage                       | BV <sub>CBO</sub>    | 180 | 220  | –    | V    | I <sub>C</sub> = 100μA   |
| Collector-Emitter Breakdown Voltage (forward blocking) | BV <sub>CEX</sub>    | 180 | 220  | –    | V    | I <sub>C</sub> = 100μA, R <sub>BE</sub> < 1kΩ or -1V < V <sub>BC</sub> > 0.25V           |
| Collector-Emitter Breakdown Voltage (Note 12)          | BV <sub>CEO</sub>    | 100 | 130  | –    | V    | I <sub>C</sub> = 10mA  |
| Emitter-Collector Breakdown Voltage (reverse blocking) | BV <sub>ECX</sub>    | 6   | 8.2  | –    | V    | I <sub>C</sub> = 100μA, R <sub>BC</sub> < 1kΩ or 0.25V < V <sub>BC</sub> > -0.25V        |
| Emitter-Collector Breakdown Voltage (reverse blocking) | BV <sub>EEO</sub>    | 6   | 8.7  | –    | V    | I <sub>E</sub> = 100μA   |
| Emitter-Base Breakdown Voltage                         | BV <sub>EBO</sub>    | 7   | 8.3  | –    | V    | I <sub>E</sub> = 100μA   |
| Collector Cut-Off Current                              | I <sub>CBO</sub>     | –   | < 1  | 50   | nA   | V <sub>CB</sub> = 180V   |
|  |                      | –   | –    | 0.5  | μA   | V <sub>CB</sub> = 180V, T <sub>A</sub> = 105°C   |
| Collector-Emitter Cut-Off Current                      | I <sub>CEX</sub>     | –   | –    | 100  | nA   | V <sub>CE</sub> = 100V, R <sub>BE</sub> < 1kΩ or -1V < V <sub>BC</sub> > 0.25V           |
| Emitter Cut-Off Current                                | I <sub>EBO</sub>     | –   | < 1  | 50   | nA   | V <sub>EB</sub> = 5.6V   |
| Collector-Emitter Saturation Voltage (Note 12)         | V <sub>CE(sat)</sub> | –   | 120  | 170  | mV   | I <sub>C</sub> = 0.5A, I <sub>B</sub> = 10mA   |
|  |                      | –   | 80   | 100  | mV   | I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA  |
|  |                      | –   | 215  | 345  | mV   | I <sub>C</sub> = 2.5A, I <sub>B</sub> = 250mA  |
|  |                      | –   | 200  | 500  | mV   | I <sub>C</sub> = 3A, I <sub>B</sub> = 600mA  |
| Base-Emitter Saturation Voltage (Note 12)              | V <sub>BE(sat)</sub> | –   | 1020 | 1100 | mV   | I <sub>C</sub> = 3A, I <sub>B</sub> = 600mA  |
| Base-Emitter Turn-On Voltage (Note 12)                 | V <sub>BE(on)</sub>  | –   | 905  | 1000 | mV   | I <sub>C</sub> = 3A, V <sub>CE</sub> = 2V  |
| DC Current Gain (Note 12)                              | h <sub>FE</sub>      | 300 | 450  | 900  | –    | I <sub>C</sub> = 10mA, V <sub>CE</sub> = 2V  |
|  |                      | 120 | 170  | –    | –    | I <sub>C</sub> = 0.5A, V <sub>CE</sub> = 2V  |
|  |                      | 40  | 60   | –    | –    | I <sub>C</sub> = 1A, V <sub>CE</sub> = 2V  |
|  |                      | –   | 10   | –    | –    | I <sub>C</sub> = 3A, V <sub>CE</sub> = 2V  |
| Current Gain-Bandwidth Product (Note 12)               | f <sub>T</sub>       | –   | 175  | –    | MHz  | V <sub>CE</sub> = 10V, I <sub>C</sub> = 50mA, f = 100MHz                                 |
| Input Capacitance (Note 12)                            | C <sub>ibo</sub>     | –   | 154  | 250  | pF   | V <sub>EB</sub> = 0.5V, f = 1MHz   |
| Output Capacitance (Note 12)                           | C <sub>obo</sub>     | –   | 8.7  | 15   | pF   | V <sub>CB</sub> = 10V, f = 1MHz  |
| Delay Time   | t <sub>d</sub>       | –   | 16.4 | –    | ns   | I <sub>C</sub> = 500mA, V <sub>CC</sub> = 10V, I <sub>B1</sub> = -I <sub>B2</sub> = 50mA |
| Rise Time  | t <sub>r</sub>       | –   | 115  | –    | ns   |  |
| Storage Time   | t <sub>s</sub>       | –   | 763  | –    | ns   |  |
| Fall Time  | t <sub>f</sub>       | –   | 158  | –    | ns   |  |

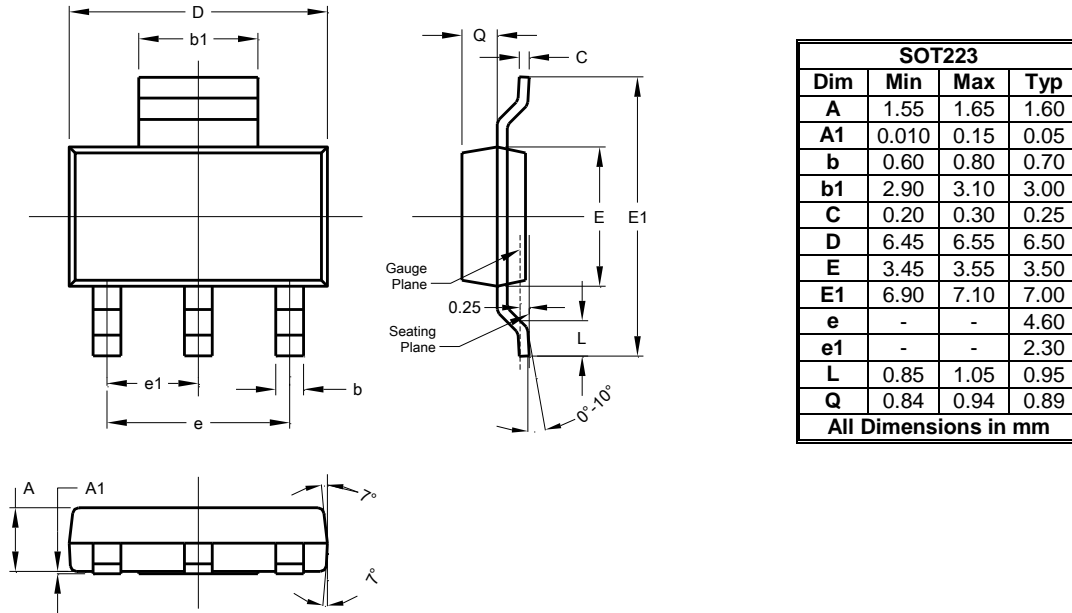
Note: 12. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

**Typical Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)



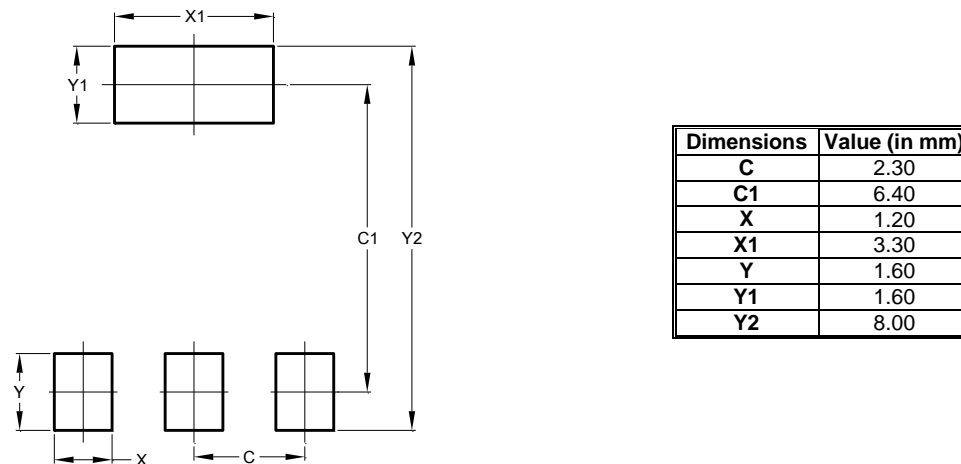
## Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.

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